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# Am27S07

64-Bit Noninverting-Output Bipolar RAM



## DISTINCTIVE CHARACTERISTICS

- Fully decoded 16-word x 4-bit low power Schottky RAMS
- Internal ECL circuitry for optimum speed/power performance over voltage and temperature
- Output preconditioned during write to eliminate the write recovery glitch
- Available with three-state outputs (Am27S07)
- Electrically tested and optically inspected die for the assemblers of hybrid products

### **GENERAL DESCRIPTION**

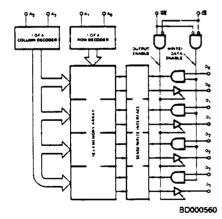
The Am27S07 is a 64-bit RAM built using Schottky diode clamped transistors in conjunction with internal ECL circuitry and is ideal for use in scratch pad and high-speed buffer memory applications. Each memory is organized as a fully decoded 16-word memory of 4 bits per word. Easy memory expansion is provided by an active LOW chip select (CS) input and three-state outputs.

An active LOW Write line (WE) controls the writing/reading operation of the memory. When the chip select and write lines are LOW the information on the four data inputs Do to D<sub>3</sub> is written into the addressed memory word and preconditions the output circuitry so that correct data is present at the outputs when the write cycle is complete. This preconditioning operation insures minimum write recovery times by eliminating the "write recovery glitch."

Reading is performed with the chip select line LOW and the write line HIGH. The information stored in the addressed word is read out on the four noninverting outputs Oo to Oo.

During the writing operation or when the chip select line is HIGH the four outputs of the memory go to an inactive high impedance state.

# **BLOCK DIAGRAM**



# MODE SELECT TABLE

In	put	Data Output	Mode		
ĊS	WE	Status O <sub>0-3</sub>			
L	L	Output Disabled	Write		
L	Н	Selected Word	Read		
H	Х	Output Disabled	Deselect		

H = HIGH

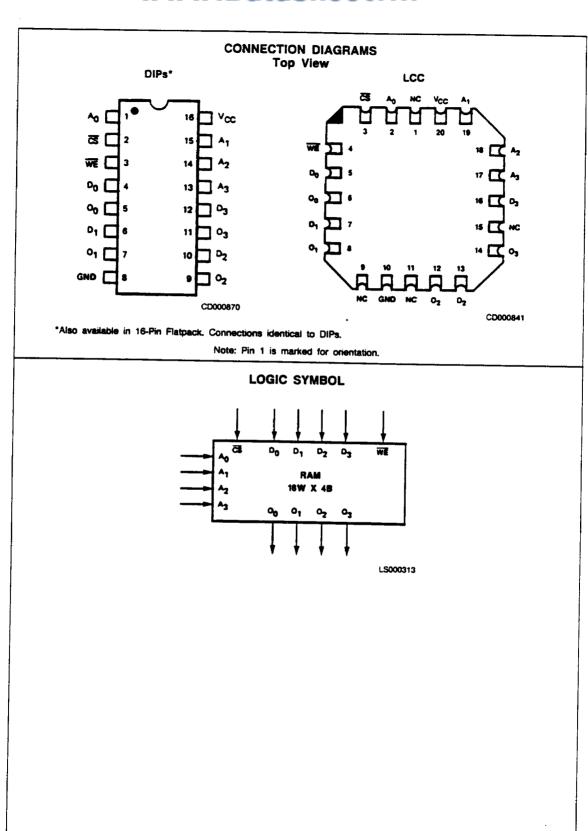
L = LOW

X = Don't Care

# PRODUCT SELECTOR GUIDE

Access Time	25 ns	30 ns	35 ns	50 ns
Icc	70 mA	70 mA	70 mA	70 mA
Temperature Range	С	M	С	М
Three-State Part Number	275	07A	27	507

Rev. <u>Amendment</u> Publication # Issue Date: February 1989

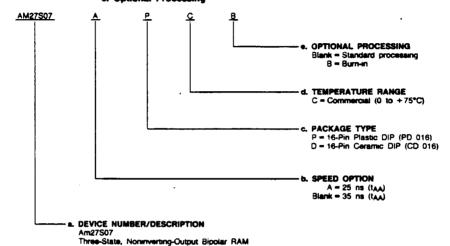


### ORDERING INFORMATION

### Standard Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of: a. Device Number

- b. Speed Option (if applicable)
- c. Package Type
- d. Temperature Range
- e. Optional Processing



# Valid Combinations AM27S07 PC, PCB, DC, DCB

AM27S07A

#### **Valid Combinations**

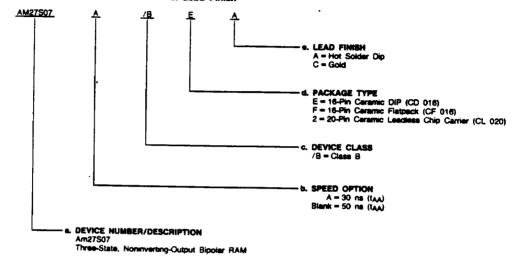
Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, to check on newly released combinations, and to obtain additional data on AMD's standard military grade products.

# MILITARY ORDERING INFORMATION

# **APL Products**

AMD products for Aerospace and Defense applications are available in several packages and operating ranges. APL (Approved Products List) products are fully compliant with MIL-STD-883C requirements. The order number (Valid Combination) for APL products is formed by a combination of: a. Device Number

- b. Speed Option (if applicable)
- c. Device Class
- d. Package Type
- e. Lead Finish



# Valid Combinations

ombinations
/BEA.
/BFA, /82A

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMO sales office to confirm availability of specific valid combinations or to check for newly released valid combinations.

### **Group A Tests**

Group A tests consist of Subgroups 1, 2, 3, 9, 10, 11.

#### **ABSOLUTE MAXIMUM RATINGS**

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Stresses above those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

### **OPERATING RANGES**

Commercial (C) Devices	
Temperature	0 to +75°C
Supply Voltage	+4.75 V to +5.25 V
Military* (M) Devices	
Temperature	
Supply Voltage	+4.5 V to +5.5 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

(See Note 5)

\*Military Product 100% tested at  $T_C = +25$ \*C, +125\*C, and -55\*C.

DC CHARACTERISTICS over operating ranges unless otherwise specified (for APL Products, Group A, Subgroups 1, 2, 3 are tested unless otherwise noted)

Parameter	Parameter					Am27S07	,	
Symbol	Description Test Conditions			Min.	Тур.	Max.	Unit	
Ver	Output HIGH	V <sub>CC</sub> = Min.,	I <sub>OH</sub> = -5.2 mA	COM'L	2.4	3.2		V
Vон	Voltage	VIN - VIH OF VIL	IOH = -2.0 mA	MIL	7 24	3.2		
Vol	Output LOW	Vcc = Min.,	IOL = 16 mA			350	450	mV
VOL	Voltage	VIN = VIH OF VIL IOL = 20 mA			380	500	m¥	
VIH	Input HIGH Level		Guaranteed Input Logical HIGH Voltage for All Inputs (Note 2)					v
ViL	Input LOW Level	Guaranteed Input Lo Voltage for All Input				0.8	٧	
1	Input LOW Current	VCC - Max.,	WE, Do-D3, Ao-A3			-15	- 250	
lit.	Input CON Curient	V <sub>IN</sub> = 0.40 V				-30	- 250	μА
ISC (Note 3)	Output Short Circuit Current	V <sub>CC</sub> = .Max., V <sub>OUT</sub> = 0.0 V	- 20	- 45	-90			
lœ	Power Supply Current	Alf Inputs = GND Outputs = Open VCC = Max.		50	70	mA		
V <sub>CL</sub>	Input Clamp Voltage	V <sub>CC</sub> = Min., I <sub>IN</sub> = -18 mA				-0.85	-1.2	٧
	VCS = VIH Or VWE=VIL Output Leakage VOUT = 2.4 V, VCC = Max.				0	40		
CEX	Current	VCS = VIH or VWE =			-40	0		μ <b>Α</b>

Notes: 1. Typical limits are at  $V_{CC} = 5.0 \text{ V}$  and  $T_A = 25^{\circ}\text{C}$ .

- These are absolute voltages with respect to device ground pin and include all overshoots due to system and/or tester noise. Do not attempt to test these values without suitable equipment.
- 3. Not more than one output should be shorted at a time. Duration of the short circuit should not be more than one second.
- Operating specification with adequate time for temperature stabilization and transverse air flow exceeding 400 linear feet per minute. Conformance testing performed instantaneously where T<sub>A</sub> = T<sub>C</sub> = T<sub>J</sub>.

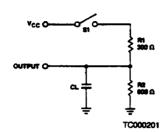
 $\theta_{\rm JA} \approx 50^{\circ}$ 9w (with moving air) for Ceramic DIP.

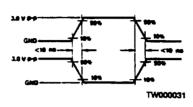
 $\theta_{\rm JC} \approx 10-17^{\circ}$ % for Flatpack and leadless chip carrier.

SWITCHING TEST CIRCUIT

SWITCHING TEST **WAVEFORM** 

**KEY TO SWITCHING WAVEFORMS** 





WAVEFORM	INPUTS	OUTPUTS
	MUST BE STEADY	WILL BE STEADY
	MAY CHANGE FROM H TO L	WILL BE CHANGING FROM H TO L
	MAY CHANGE FROM L TO H	WILL BE CHANGING FROM L TO H
XXXX	DON'T CARE: ANY CHANGE PERMITTED	CHANGING: STATE UNKNOWN
₩	DOES MOT APPLY	CENTER LINE IS HIGH IMPEDANCE "DFP" STATE
		VC000040

KS000010

SWITCHING CHARACTERISTICS over operating range unless otherwise specified (for APL Products, Group A, Subgroups 9, 10, 11 are tested unless otherwise noted)

No. Parameter Symbol		A	Am27S06A/27S07A			Am27S06/27S07				T	
	Parameter Description	C Devices		M Devices		C Devices		M Devices		†	
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units	
1	tpLH(A)	Deleu from Address to Outside				<b></b>					
2	IPHL(A)	Delay from Address to Output		25		30	ł	35		50	ns
3	tpzH(CS)	Delay from Chip Select (LOW) to		15		20	<u> </u>			<del> </del>	<del>                                     </del>
4	tpzt(CS)	Active Output and Correct Data		13		20	ļ	17		25	ns
5	tpZH(WE)	Delay from Write Enable (HIGH) to Active Output and Correct Data		20					<u> </u>		
6	tpZL(WE)	(Write Recovery-See Note 1)	•	20	Ī	25		35		40	ns
7	t <sub>s</sub> (A)	Setup Time Address (Prior to Initiation of Write)	0		0		0		0		ns
8	th(A)	Hold Time Address (After Termination of Write)	0		0		0		0		nş
9	t <sub>s</sub> (DI)	Setup Time Data Input (Prior to Termination of Write)	20		25		25		25		ns
10	<b>հ</b> (OI)	Hold Time Data Input (After Termination of Write)	0		0		0		0		ns
11	tpw(WE)	MIN Write Enable Width Pulse to Insure Write	20		25		25		25		ns
12	tpHZ(CS)	Delay from Chip Select (HIGH)		15							
13	(PLZ(CS)	to inactive Output (HI-Z)		15		20		17		25	п\$
14	tp <u>LZ(WE)</u>	Delay from Write Enable (LOW)		20		-					
15	tpHZ(WE)	to Inactive Output (HI-Z)	ı	40		25		25		35	ns

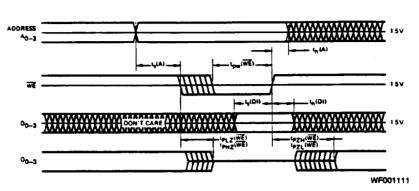
Notes: 1. Output is preconditioned to data in during write to insure correct data is present on all outputs when write is terminated. (No write recovery glitch.)

recovery gitten.)

2. tpLH(A) and tpHL(A) are tested with S₁ closed and CL = 30 pF with both input and output timing referenced to 1.5 V.

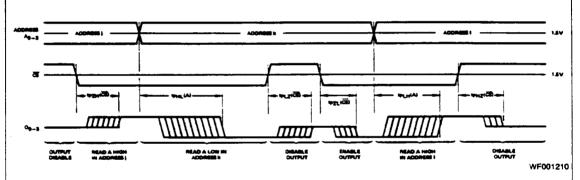
3. For 3-state output, tpZH(WE) and tpZH(CS) are measured with S₁ open, CL = 30 pF and with both the input and output timing referenced to 1.5 V. tpZL(WE) and tpZL(CS) are measured with S₁ closed, CL = 30 pF and with both the input and output timing referenced to 1.5 V. tpHZ(WE) and tpHZ(CS) are measured with S₁ open and CL ≤ 5 pF and are measured between the 1.5 V level on the output. tpLZ(WE) and tpLZ(CS) are measured with S₁ closed and CL ≤ 5 pF and are measured between the 1.5 V level on the input and the VOL+500 mV level on the output.





### Write Mode

Write Cycle Timing. The cycle in initiated by an address change. After  $t_s(A)$ min, the write enable may begin. The chip select must also be LOW for writing. Following the write pulse,  $t_h(A)$ min must be allowed before the address may be changed again. The output will be floating for the Am27S07 while the write enable is LOW.



## Read Mode

Switching delays from address and chip select inputs to the data output. For the Am27S07 disabled output is "OFF", represented by a single center line.